

# **isc Silicon NPN Power Transistor**

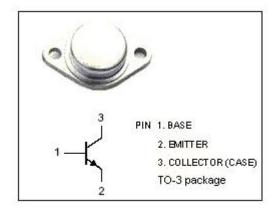
### **DESCRIPTION**

- · High Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= 800V (Min)
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

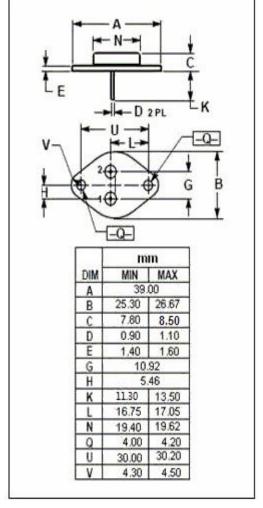


 Designed for high voltage, high speed and high power applications.



# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	MAX	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	1500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
lc	Collector Current-Continuous	5	А
Ісм	Collector Current-Peak	7	Α
I <sub>B</sub>	Base Current-Continuous	2.5	Α
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	80	W
T <sub>j</sub>	unction Temperature 150		$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range	-45~150	$^{\circ}$ C





## isc Silicon NPN Power Transistor

2SC2928

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

T <sub>C</sub> =25°C unless otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustainig Voltage	I <sub>C</sub> =1mA; I <sub>B</sub> =0	800			V			
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10mA; I <sub>C</sub> = 0	7			٧			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1.5A; I <sub>B</sub> = 0.3A			1.0	٧			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1.5A; I <sub>B</sub> = 0.3A			1.5	٧			
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	15						
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	7						
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1200V; I <sub>E</sub> = 0			0.1	mA			
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 650V; R <sub>BE</sub> = ∞			0.1	mA			
Switching T	Times								
t <sub>on</sub>	Turn-On Time				1.0	μS			
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 3A; I <sub>B1</sub> = 0.6A; I <sub>B2</sub> = -1.5A; V <sub>CC</sub> ≈ 250V			3.0	μS			
t <sub>f</sub>	Fall Time				1.0	μS			

#### Notice:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.